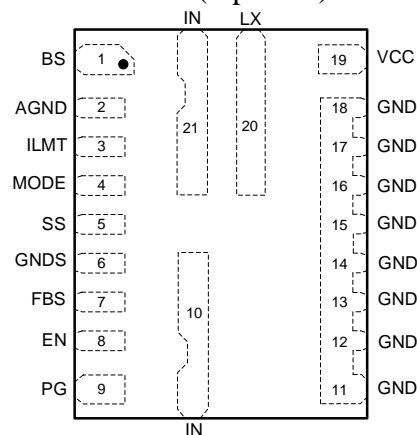


Ordering Information

Ordering Part Number	Package Type	Top Mark
SQ29072TXQ	QFN3×4-21 RoHS Compliant and Halogen Free	EAB _{xyz}

x=year code, y=week code, z= lot number code

Pinout (top view)



Pin No	Pin Name	Pin Description
1	BS	Boot-strap supply for the high side gate driver. Connect a 0.1μF ceramic capacitor between the BS and the LX pin.
2	AGND	Analog ground.
3	ILMT	Synchronous rectifier current limit setting. Connect a resistor to AGND to set the inductor valley current limit value.
4	MODE	Operation mode selection. Program MODE to select FCCM/PFM, and the operating switching frequency. See table 1.
5	SS	External soft-start setting. Optionally adjust the soft-start time by adding an appropriate external capacitor between this pin and AGND pin. See Detailed Description.
6	GNDS	Remote ground sense. Connect this pin directly to the negative side of the preferred voltage sense point. Short to AGND if remote sense is not used.
7	FBS	Remote feedback sense. Connect this pin to the center point of the output resistor divider to program the output voltage. See Design Procedure.
8	EN	Enable input. Pull low to disable the device, high to enable. Do not leave this pin floating. May be used for increasing startup voltage or sequencing. See Detailed Description.
9	PG	Power good indicator. Open drain output when the output voltage is within 93.5% to 120% of the regulation set point.
10, 21	IN	Power input. Decouple this pin to GND pin with at least a 20μF ceramic capacitor.
11, 12, 13, 14, 15, 16, 17, 18	GND	Power ground.
19	VCC	Internal 3.3V LDO output. Power supply for internal analog circuits and driving circuits. Decouple this pin to GND with at least a 1μF ceramic capacitor. Use short, direct connections and avoid the use of vias. May be driven by an external bias supply. See Detailed Description.
20	LX	Inductor pin. Connect this pin to the switching node of the inductor.

Block Diagram

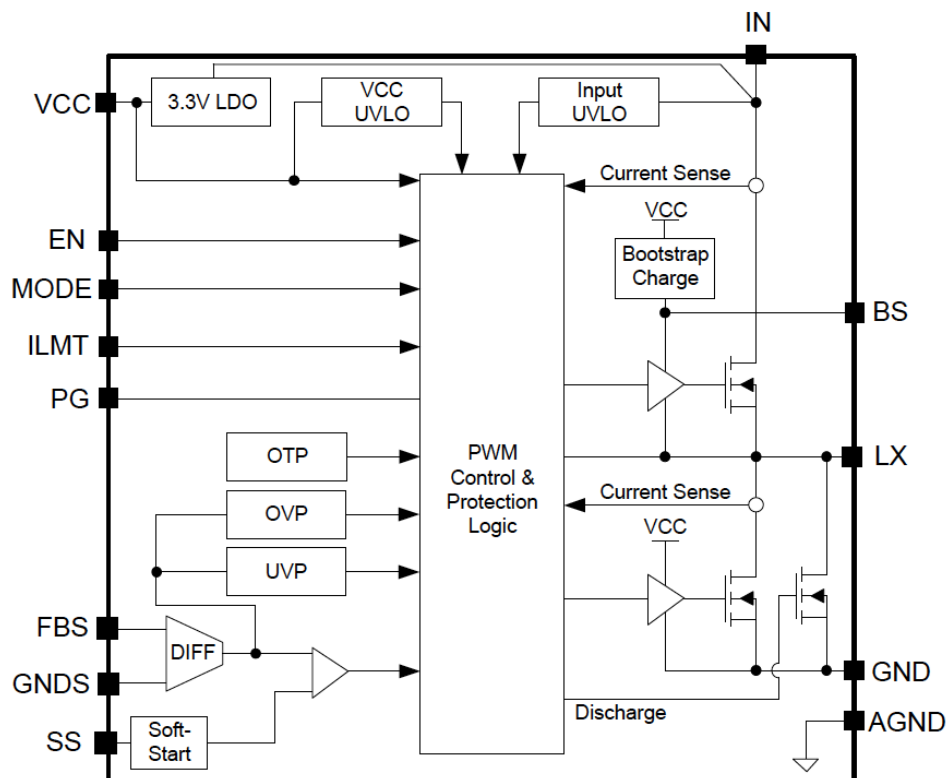


Figure 3. Block Diagram

Absolute Maximum Ratings (1)	Min	Max	Unit
IN	-0.3	18	V
ILMT, EN, MODE, SS, LX	-0.3	IN + 0.3	
LX, 10ns duration	-5	IN + 5	
BS	LX - 0.3	LX + 4	
FBS, GNDS, AGND, VCC, PG	-0.3	4	°C
Junction Temperature, Operating	-40	150	
Lead Temperature(Soldering,10sec.)		260	
Storage Temperature	-65	150	

Thermal Information (2)	Typ	Unit
θ_{JA} Junction-to-ambient Thermal Resistance	25	°C/W
θ_{JC} Junction-to-case Thermal Resistance	5	
P_D Power Dissipation $T_A=25^{\circ}\text{C}$	4	W

Recommended Operating Conditions (3)	Min	Max	Unit
IN	2.7	16	V
Output Voltage	0.6	5.5	
GNDS	-0.2	0.2	
Output Current		12	A
Output Current Limit Setting		14	
Peak Inductor Current		17	
Junction Temperature	-40	125	°C

Electrical Characteristics $V_{IN} = 12V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, typical values are at $T_J = 25^{\circ}C$, unless otherwise specified (4)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Input	Voltage	V _{IN}		2.7		16	V
	UVLO, rising	V _{IN,UVLO}		2.52	2.6	2.68	V
	UVLO, Hysteresis	V _{IN,HYS}			200		mV
	Shutdown Current	I _{SHDN}	V _{EN} =0V, T _J =25°C		3	5	μA
	Quiescent Current	I _Q	V _{EN} =2V, V _{FBS} = 0.65V, PFM mode, No Switching		650	850	μA
VCC	UVLO, Rising	V _{VCC,UVLO}				2.5	V
	UVLO, Hysteresis	V _{VCC,HYS}			100		mV
	Output	V _{CC}	I _{VCC} =0mA	3.1	3.25	3.4	V
	Load regulation	V _{CC,REG}	I _{VCC} =25mA		1.8		%
FBS	Reference Voltage	V _{REF}	GNDS = 0V	0.594	0.600	0.606	V
	Error Amp Offset	V _{OS}		-3		3	mV
	Input Current	I _{FBS}	V _{EN} =2V, V _{FBS} = 1V	-50	0	50	nA
Power Switch	On resistance	R _{DS(ON)HS}	V _{BS-LX} = 3.3V, T _J =25°C		12.6	18.9	mΩ
	Current Limit	I _{LMT,HS}		14	15.5	17	A
Synchronous Rectifier	On resistance	R _{DS(ON)LS}	V _{CC} = 3.3V, T _J =25°C		4.3	6.5	mΩ
	Reverse current	I _{LMT,RVS}		3.5	4.5	6.6	A
		t _{RCL,BLK}		40	60		ns
	Forward current	I _{LMT,BOT}	R _{ILMT} = 4.5kΩ		13.3		A
ILMT Pin Output Voltage		V _{ILMT}		0.77	0.8	0.83	V
ILMT Ratio		I _{ILMT} /I _{LMT,BOT}	I _{LMT,BOT} >5A	12	13.3	14.6	μA/A
Discharge FET Resistance		R _{DIS}			60		Ω
Enable (EN)	Rising Threshold	V _{EN,R}		1.16	1.21	1.26	V
	Threshold Hysteresis	V _{EN,HYS}			0.23		V
	Input Current	I _{EN}	V _{EN} =2V		0		μA
Soft Start (SS)	Charging current	I _{SS1}	V _{SS} =0V		42		μA
	Discharge current	I _{SS2}	V _{SS} =1V		34		mA
	Min soft-start time	t _{SS,MIN}			1		ms
Overvoltage Protection Threshold		V _{OVP}		110	120	130	% V _{FBS}
Undervoltage Protection	threshold	V _{UVP}		45	50	55	
	Delay	t _{UVP,DLY}			20		μs
UVP/OCP Hiccup ON Time		t _{HICCUP,ON}	C _{SS} open		3		ms
UVP/OCP Hiccup OFF Time		t _{HICCUP,OFF}			15		
Power Good	Thresholds	V _{PG}	V _{FBS} falling, fault	76	79	82.5	% V _{FBS}
			V _{FBS} rising, good	88	93.5	97	
			V _{FBS} rising, fault	110	120	130	
			V _{FBS} falling, good	100	103.5	107.5	
	Delay	t _{PG,R}	V _{FBS} rising, good		0.8		ms
			t _{PG,F}	V _{FBS} falling, fault		20	
	Output low voltage	V _{PG,LOW}	V _{IN} =0V, 100kΩ from PG to 3.3V		550	750	mV
			V _{IN} =0V, 10kΩ from PG to 3.3V		660	850	
			V _{EN} = 2V, V _{FBS} = 0V, I _{PG} =10mA			0.4	V
Output low leakage		I _{PG,LKG}	V _{PG} = 3.3V		3	5	μA

Electrical Characteristics (cont.) $V_{IN} = 12V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, typical values are at $T_J = 25^{\circ}C$, unless otherwise specified (4)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Switching Frequency	f_{SW}	$R_{MODE}=0\Omega$, $I_{OUT}=0A$, FCCM, $V_{OUT}=1V$, $T_J=25^{\circ}C$	500	600	700	kHz
		$R_{MODE}=30.1k\Omega$, $I_{OUT}=0A$, FCCM, $V_{OUT}=1V$, $T_J=25^{\circ}C$	710	800	890	
		$R_{MODE}=60.4k\Omega$, $I_{OUT}=0A$, FCCM, $V_{OUT}=1V$, $T_J=25^{\circ}C$	900	1000	1100	
Min ON Time	$t_{ON,MIN}$	$I_{OUT}=3A$		55		ns
Min OFF Time	$t_{OFF,MIN}$	$I_{OUT}=3A$		150		
Thermal Shutdown Temperature	T_{SD}		140	160		$^{\circ}C$
Thermal Shutdown Hysteresis	T_{HYS}			30		

Note 1: Stresses beyond the “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

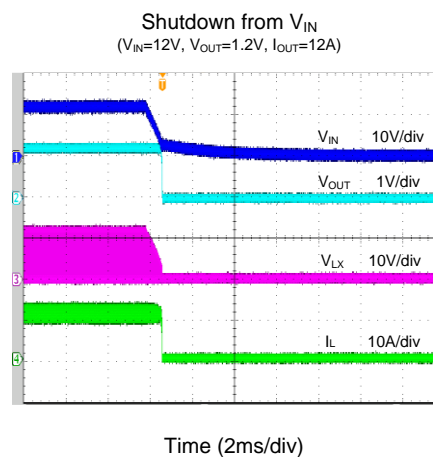
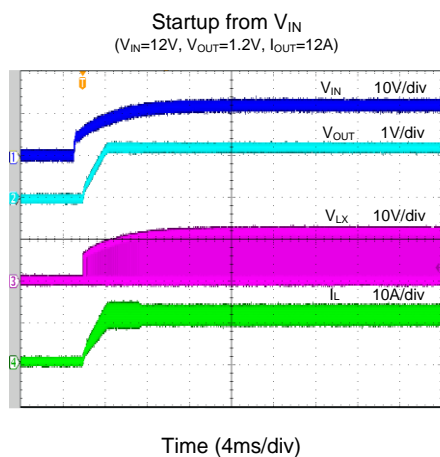
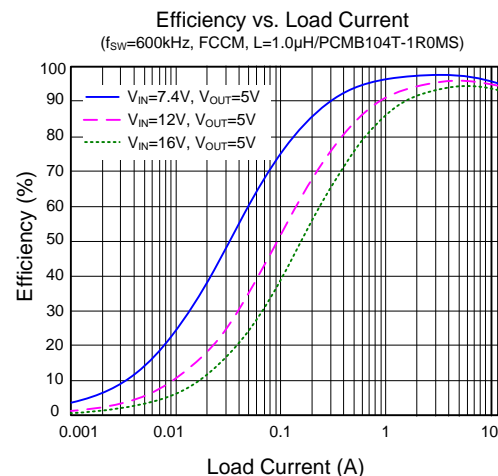
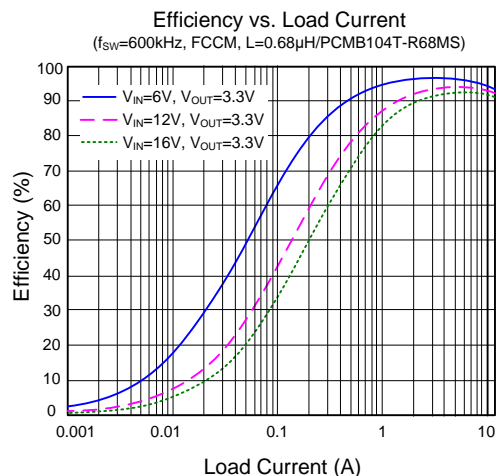
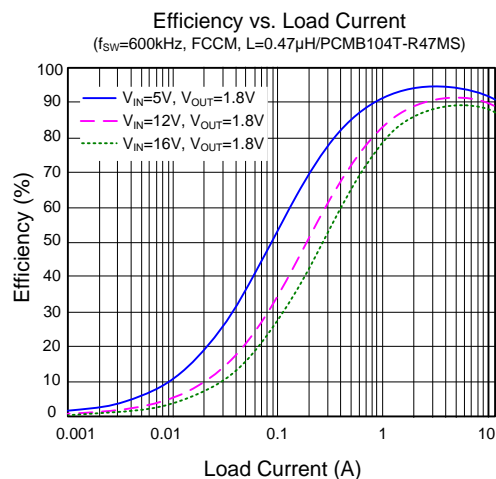
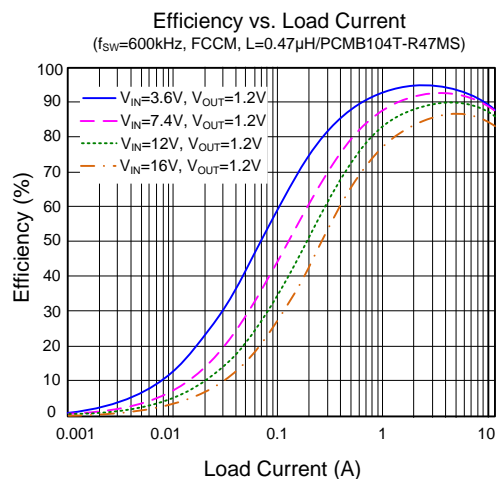
Note 2: Package thermal resistance is measured in the natural convection at $T_A=25^{\circ}C$ on an 8.5cm×8.5cm size four-layer Silergy Evaluation Board.

Note 3: The device is not guaranteed to function outside its operating conditions.

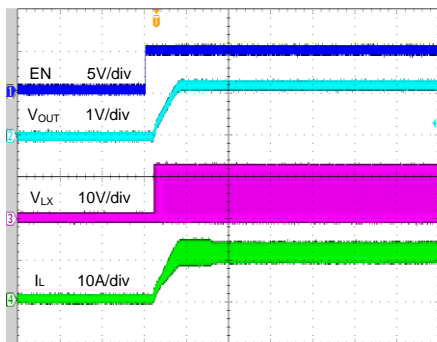
Note 4: Production testing is performed at $25^{\circ}C$; limits at $-40^{\circ}C$ to $+125^{\circ}C$ are guaranteed by design, test or statistical correlation.

Typical Performance Characteristics

($T_A=25^{\circ}\text{C}$, $V_{IN}=12\text{V}$, $V_{OUT}=1.2\text{V}$, $L=0.47\mu\text{H}$, $C_{OUT}=44\mu\text{F}$, $f_{SW}=600\text{kHz}$, $R_{ILMT}=4.5\text{k}\Omega$, $C_{SS}=0.22\mu\text{F}$, unless otherwise noted)

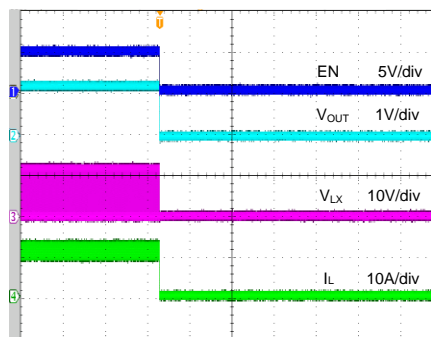


Startup from EN
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=12A$)



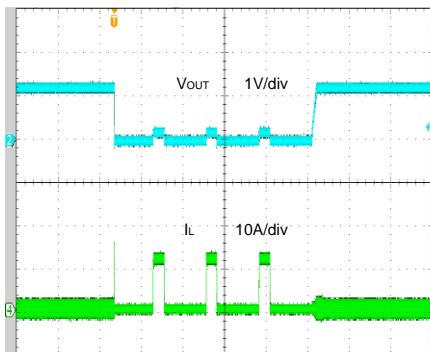
Time (4ms/div)

Shutdown from EN
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=12A$)



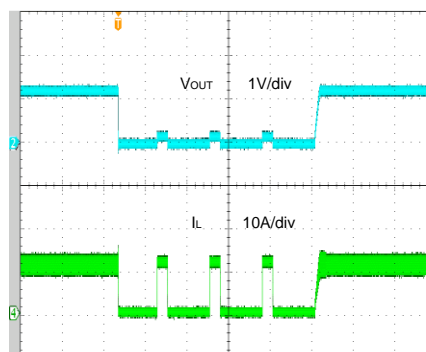
Time (4ms/div)

Short Circuit Protection
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$ -short, $R_{ILMT}=4.5k\Omega$, FCCM)



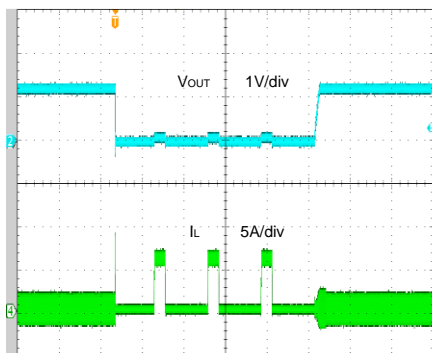
Time (20ms/div)

Short Circuit Protection
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=12A$ -short, $R_{ILMT}=4.5k\Omega$, FCCM)



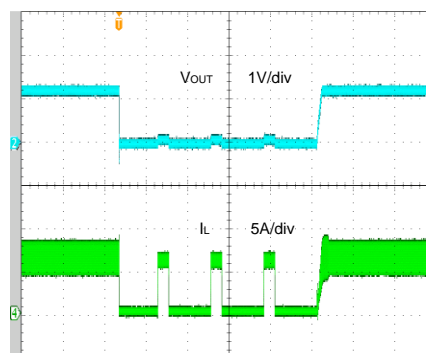
Time (20ms/div)

Short Circuit Protection
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$ -short, $R_{ILMT}=10k\Omega$, FCCM)



Time (20ms/div)

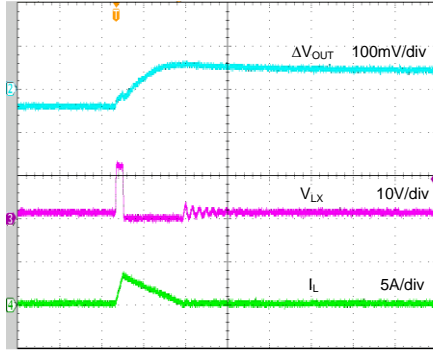
Short Circuit Protection
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=6A$ -short, $R_{ILMT}=10k\Omega$, FCCM)



Time (20ms/div)

Output Ripple

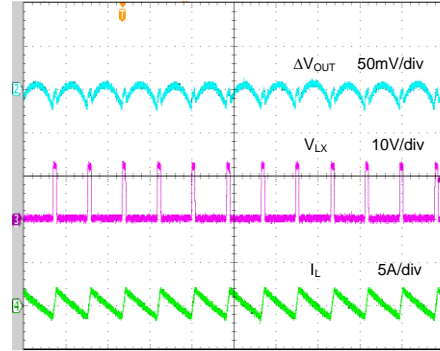
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$, PFM)



Time (1μs/div)

Output Ripple

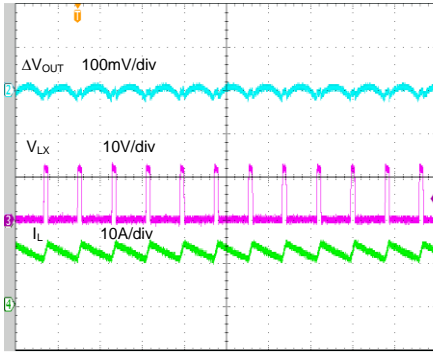
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=0A$, FCCM)



Time (2μs/div)

Output Ripple

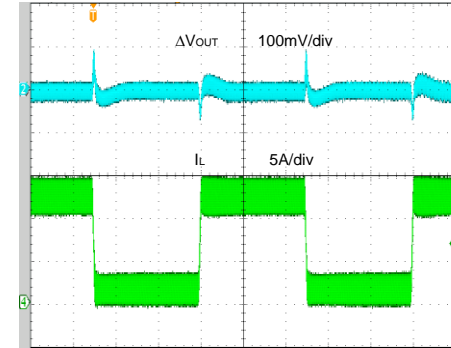
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=12A$)



Time (2μs/div)

Load Transient

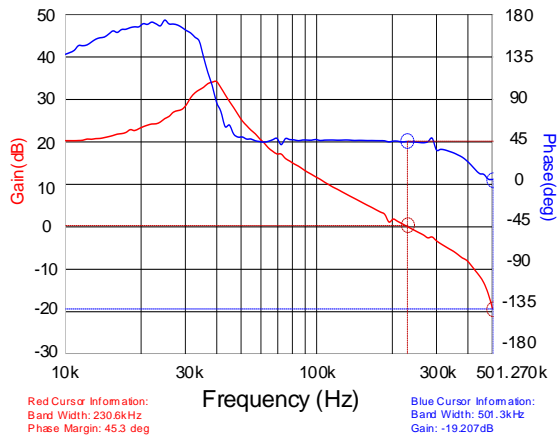
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=1.2\sim12A$, FCCM)



Time (200μs/div)

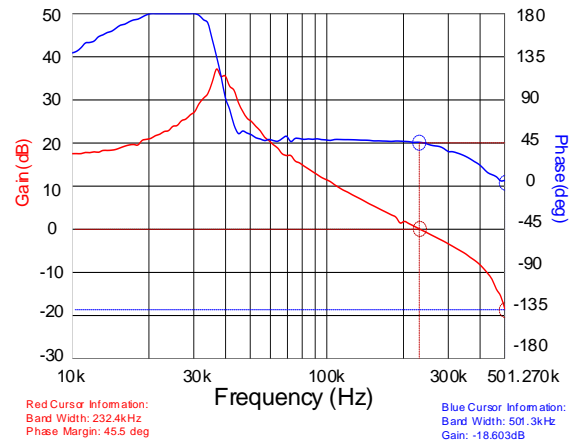
Bode Plot

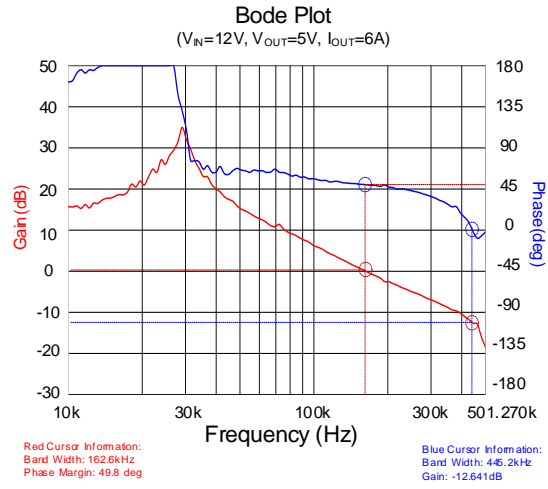
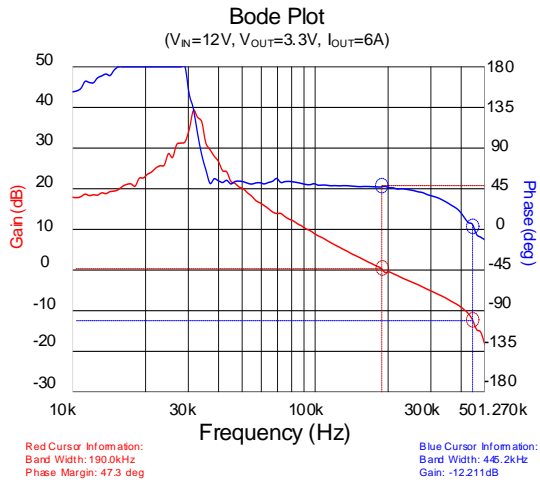
($V_{IN}=12V$, $V_{OUT}=1.2V$, $I_{OUT}=6A$)



Bode Plot

($V_{IN}=12V$, $V_{OUT}=1.8V$, $I_{OUT}=6A$)





Detailed Description

General Features

Constant-on-time Architecture and Frequency Lock

Loop(FLL)

Fundamental to any constant-on-time (COT) architecture is the one-shot circuit or on-time generator, which determines how long to turn on the high-side power switch. Each on-time (t_{ON}) is a “fixed” period internally calculated to operate the step down regulator at the desired switching frequency considering the input and output voltage ration, $t_{ON} = (V_{OUT}/V_{IN}) \times (1/f_{SW})$. For example, considering that a hypothetical converter targets 1.2V output from a 12V input at 600kHz, the target on-time is $(1.2V/12V) \times (1/600kHz) = 167ns$. Each t_{ON} pulse is triggered by the feedback comparator when the output voltage as measured at FB drops below the target value. After one t_{ON} period, a minimum off-time ($t_{OFF,MIN}$) is imposed before any further switching is initiated, even if the output voltage is less than the target. This approach avoids the making any switching decisions during the noisy periods just after switching events and while the switching node (LX) is rapidly rising or falling.

In a COT architecture, there is no fixed clock, so the high-side power switch can turn on almost immediately after a load transient and subsequent switching pulses can be quickly initiated, ramping the inductor current up to meet load requirements with minimal delays. Traditional current mode or voltage mode control methods must simultaneously monitor the feedback voltage, current feedback and internal ramps and compensation signals to determine when to turn off the high-side power switch and turn on the low-side synchronous rectifier. Considering these small signals in a switching environment are difficult to be noise-free after switching large currents, making those architectures difficult to apply in noisy environments and at low duty cycles.

On one hand, once the on-time calculated by the constant-on-time architecture has one deviation from the accurate on-time value, especially in the case of small duty cycle operation, the actual switching frequency will deviate from the setting value largely. On the other hand, when the load is close to full load, the duty cycle loss will also cause switching frequency deviation. In order to maintain the switching frequency constant relatively under different application conditions, the constant-on-time architecture needs one frequency lock loop (FLL). In the PLL, the reference frequency is one fixed clock, keeps the same as the setting frequency, and the switching frequency is compared with it cycle by cycle. This loop will adjust the actual on-time, let the switching frequency follow the reference frequency until there is no deviation between them. This FLL function is disabled during soft-start process and discontinuous current mode (DCM) condition. Before soft-start process is done, the CCM switching frequency is

equal to one initial frequency, which is a little bit less than the reference frequency.

Instant-PWM Operation

Silergy's instant-PWM control method adds several proprietary improvements to the traditional COT architecture. Whereas most legacy based on COT implementations require a dedicated connection to the output voltage terminal to calculate the t_{ON} duration, instant-PWM control method derives this signal internally. Another improvement optimizes operation with low ESR ceramic output capacitors. In many applications it is desirable to utilize very low ESR ceramic output capacitors, but legacy COT regulators may become unstable in these cases because the beneficial ramp signal that results from the inductor current flowing into the output capacitor maybe become too small to maintain smooth operation. For this reason, instant-PWM synthesizes a virtual replica of this signal internally. This internal virtual ramp and the feedback voltage are combined and compared to the reference voltage. When the sum is lower than the reference voltage, the t_{ON} pulse is triggered as long as the minimum t_{OFF} has been satisfied and the inductor current as measured in the low-side synchronous rectifier is lower than the bottom FET current limit. As the t_{ON} pulse is triggered, the low-side synchronous rectifier turns off and the high-side power switch turns on. Then the inductor current ramps up linearly during the t_{ON} period. At the conclusion of the t_{ON} period, the high-side power switch turns off, the low-side synchronous rectifier turns on and the inductor current ramps down linearly. This action also initiates the minimum t_{OFF} timer to ensure sufficient time for stabilizing any transient conditions and settling the feedback comparator before the next cycle is initiated. This minimum t_{OFF} is relatively short so that during high speed load transient t_{ON} can be retrIGGERED with minimal delay, allowing the inductor current to ramp quickly to provide sufficient energy to the load side.

In order to avoid shoot-through, a dead time (t_{DEAD}) is generated internally between the high-side power switch off and the low-side synchronous rectifier on period or the low-side synchronous rectifier off and the high-side power switch on period.

Light Load Operation Mode and Switching Frequency Selection

PFM or FCCM light load operation mode and switching frequency are both selected by MODE pin. Once the light load operation mode and switching frequency is selected after VCC set up, then it will be locked unless the device shuts down. See the following table.

Table 1

MODE Pin Connection	Light-Load Mode	Switching Frequency
VCC	PFM	600kHz
240kΩ(±20%) to GND	PFM	800kHz
120kΩ(±20%) to GND	PFM	1000kHz
GND	FCCM	600kHz
30kΩ(±20%) to GND	FCCM	800kHz
60kΩ(±20%) to GND	FCCM	1000kHz

If PFM light load operation is selected, under light load conditions, typically $I_{OUT} < 1/2 \times \Delta I_L$, the current through the low-side synchronous rectifier will ramp to near zero before the next t_{ON} time. When this occurs, the low-side synchronous rectifier turns off, preventing recirculation current that can seriously reduce efficiency under these light load conditions. As load current is further reduced, and the combined feedback and ramp signals remain much greater than the reference voltage, the instant-PWM control loop will not trigger another t_{ON} until needed, so the apparent operating switching frequency will correspondingly drop, further enhancing efficiency. The switching frequency can be lower than audible frequency area under deep light load or null load conditions. Continuous conduction mode (CCM) resumes smoothly as soon as the load current increases sufficiently for the inductor current to remain above zero at the time of the next t_{ON} cycle. The device enters CCM once the load current exceeds the critical level. After that, the switching frequency stays fairly constant over the output current range. The critical level of the load current is determined with

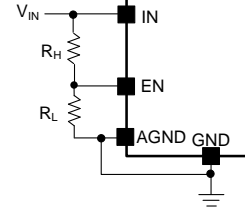
$$I_{OUT_CTL} = \frac{\Delta I_L}{2} = \frac{V_{OUT} \times (1-D)}{2 \times f_{SW} \times L_1}$$

If FCCM light load operation is selected, under light load conditions, the low-side synchronous rectifier still turns on even when the inductor current crosses zero. Current flow will continue until the next t_{ON} cycle. The device always operates under continuous conditions mode and keeps fairly constant switching frequency over all the output current range.

Input Under Voltage Lock-out (UVLO)

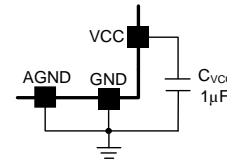
To prevent operation before all internal circuitry is ready and to ensure that the power and synchronous rectifier switches can be sufficiently enhanced, the instant-PWM incorporates one input under-voltage lockout protections. The device remains in a low current state and all switching actions are inhibited until V_{IN} exceeds their own UVLO (rising) threshold. At that time, if EN is enabled, the device will start-up by initiating a soft-start ramp. If V_{IN} falls below $V_{IN,UVLO}$ less than the input UVLO hysteresis, switching actions will again be suppressed.

If the input UVLO threshold is low for some high input UVLO threshold requirement applications, use EN to adjust the input UVLO by adopting two external divided resistors.



VCC Linear Regulator and VCC UVLO

The SQ29072 integrates one high performance, low drop-out linear regulator 3.3V VCC, supplied by input voltage, which can power the internal gate drivers, PWM logic, analog circuitry and other blocks. Connect a 1μF low ESR ceramic capacitor from VCC to GND.



Like input UVLO design, VCC has also one UVLO protection. When the VCC voltage is lower than VCC UVLO rising threshold for one VCC UVLO hysteresis, the device will shut down to ensure all internal circuitry logic is right and the power and synchronous rectifier switches can be sufficiently enhanced.

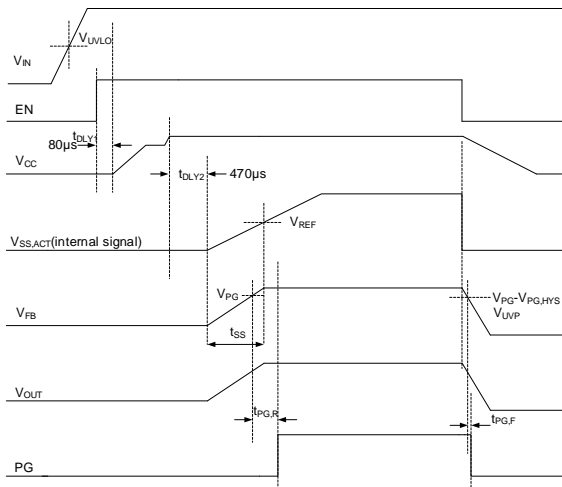
Enable Control

The EN input is a high-voltage capable input with logic-compatible threshold. The comparator design scheme makes the EN rising threshold accurate comparatively. When EN voltage rises to ~0.8V, VCC works so that the EN comparator has source supply. When EN is driven above 1.21V normal device operation will be enabled, and the switching node pulse appear. When EN voltage falls lower than EN rising threshold for one hysteresis, the switching node pulse is inhibited. When EN voltage is driven < 0.4V the VCC will be shut down, reducing input current to <5μA (Normal temperature).

It is not recommended to connect EN and IN directly. A resistor in a range of 1kΩ to 1MΩ should be used if EN is pulled high by IN.

Startup and Shutdown

The SQ29072 incorporates an internal soft-start circuit to smoothly ramp the output to the desired voltage whenever the device is enabled. Internally, the soft-start circuit clamps the output at a low voltage and then allows the output to rise to the desired voltage over approximately one soft-start time, which avoids high current flow and transients during startup. The startup and shutdown sequence is shown below.



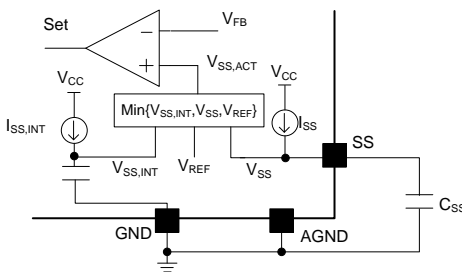
After the input voltage exceeds its own UVLO (rising) threshold, V_{CC} is turned on after EN is enabled for a delay time t_{DLY1} , the buck regulator is turned on after another delay time t_{DLY2} after V_{CC} voltage is set up. When the output voltage is 93.5% of the regulation point, PG becomes high-impedance after a delay time $t_{PG,R}$.

Programmable Soft-start Time and On-time Pre-bias Function

The soft-start time can be programmable by SS pin. Connect one capacitor between SS pin and AGND pin to program the soft-start time. The actual soft-start time is determined by the slower rising slew rate of the external SS voltage V_{SS} and internal SS voltage $V_{SS,INT}$. The soft-start time equation is:

$$t_{SS}(\text{ms}) = \frac{C_{SS}(\text{nF}) \times V_{REF}}{I_{SS}(\mu\text{A})}$$

The typical value of SS charging current I_{SS} is 42µA. To guarantee the programmable soft-start time is not too short when using smaller SS capacitor, there is one minimum soft-start time limitation, the minimum soft-start time is 1ms.



When under voltage protection (UVP) occurs, the hiccup on time and hiccup off time is also determined by the slower SS voltage slew rate, but the time ratio keeps still 1:5.

If the output is pre-biased to a certain voltage before start-up, the device disables the switching of both the high-side power switch and the low-side synchronous rectifier until the voltage

on the internal soft start circuit voltage $V_{SS,ACT}$ exceeds the sensed output voltage at the FB node. Before the switching node pulse occurs, the switching node voltage is sampled to internal on-time generator circuit to make on-time pre-bias, in order to the first on-time will be matched with the current pre-bias output voltage.

What is worth mentioning, in the output voltage pre-biased scenario, if the BS-LX voltage is lower than 1.8V, the low-side synchronous rectifier turns on to allow the BS voltage to be charged by V_{CC} . The low-side synchronous rectifier turns on just for one very narrow pulse, so the drop in the pre-biased output level is negligible.

Differential Output Voltage Remote Sense Function

The device supports differential remote output voltage sense function. The dedicated GNDS pin helps provide the remote GND voltage sense, cooperating with remote OUT voltage sense in order to prevent the remote load side's voltage decrease largely even the load current is high up to 12A. The pair of the remote sense trace should be kept in low impedance to achieve the best performance.

Output Discharge Function

The SQ29072 discharges the output voltage when the converter shuts down from V_{IN} or EN, or thermal shutdown, so that output voltage can be discharged in a minimal time, even load current is zero. The discharge FET in parallel with the low-side synchronous rectifier turns on after the low-side synchronous rectifier turns off when shut down logic is triggered. The output discharge FET $R_{DS(ON)}$ is typically 60Ω under room temperature. Note that the discharge FET is not active beyond these shutdown conditions.

Buck Output Power Good Indicator

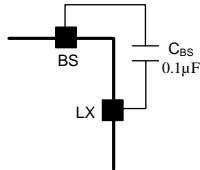
The Buck power good indicator is an open drain output controlled by a window comparator connected to the feedback signal. If V_{FB} is greater than $V_{PG,R}$ and less than V_{OVF} for at least the power good delay time (low to high), PG will be high-impedance.

PG should be connected to V_{CC} or another voltage source less than 4V through a resistor (e.g. 10kΩ~100kΩ). After V_{IN} exceeds its own UVLO (rising) threshold, the PG FET is turned on so that PG is pulled to GND before output voltage is ready. After feedback voltage V_{FB} reaches $V_{PG,R}$, PG is pulled high (after a delay time within 800µs). When V_{FB} drops to $V_{PG,F}$, or rises to V_{OVF} for one OVP delay time, PG is pulled low (after a delay time within 20µs).

PG circuit adopts special design, when the PG connects with external power source through 10kΩ~100kΩ, even the input voltage is zero, the PG voltage keeps one output low voltage level.

External Bootstrap Capacitor Connection

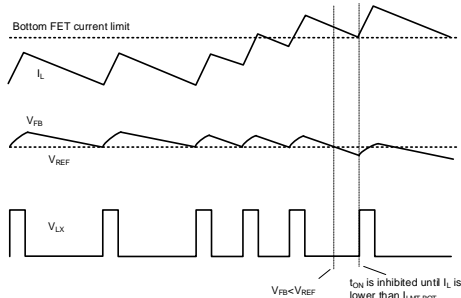
This device integrates a floating power supply for the gate driver that operates the high-side power switch. Proper operation requires a 0.1μF low ESR ceramic capacitor to be connected between BS and LX. This bootstrap capacitor provides the gate driver supply voltage for the high-side N-channel MOSFET power switch.



Fault Protection Modes

Programmable Valley Current Limit Protection

Instant-PWM incorporates a cycle-by-cycle “valley” current limit. Inductor current is measured in the low-side synchronous rectifier when it turns on and as the inductor current ramps down. If the current exceeds the bottom FET current limit, t_{ON} is inhibited until the current returns back to safe levels.

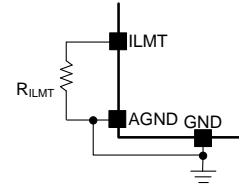


The OCP limits the inductor current but the device does not latch off. Under an over current condition, the current to the load exceeds the current to the output capacitor, thus the output voltage tends to fall off. Eventually, it will end up with crossing the under voltage protection (UVP) threshold and the device will latch off. On the other hand, over temperature protection may also be triggered under an over-current condition and the device will latch off. Overall, the device tends to trigger UVP or OTP latch off protection under an over current condition and OCP itself is not latch off protection.

The valley current limit point can be programmable by ILMT pin. Connect one resistor from ILMT pin to the AGND pin to program valley current limit point. The ILMT output voltage is constant, the ILMT resistor current is sensed by the device, comparing with low-side synchronous rectifier current mirror value. If the mirror current is larger than the ILMT resistor current, the device works under valley current limit state and t_{ON} is inhibited. The valley current limit point equation is

$$I_{BOT,LMT} = \frac{V_{ILMT}}{G_{MIRROR} \times R_{ILMT} (\Omega)}$$

Where, ILMT output voltage V_{ILMT} is 0.8V, the low-side synchronous rectifier mirror ratio G_{MIRROR} is 13.3μA/A typically.



Peak Current Limit Protection

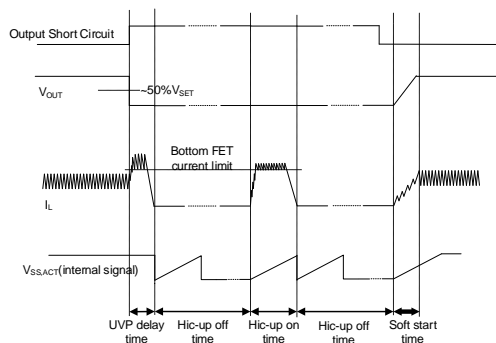
The device also features cycle-by-cycle “peak” current limit (top FET current limit). During t_{ON} time, the high-side power switch current is monitored. If the monitored current exceeds the top FET current limit, the high-side power switch is turned off, the low-side synchronous rectifier is turned on and then t_{ON} is inhibited. t_{ON} can be not inhibited any more once low-side synchronous rectifier current is lower than the bottom FET current limit value. Peak current limit protection has one blank time, at the initial on-time, high-side power switch current sample is disabled to make sampling noise shielding. Peak current limit protection priority is lower than minimum on-time.

Reverse Current Limit Protection

The device also features cycle-by-cycle “reverse” current limit. When the device works under FCCM mode, the low-side synchronous rectifier current is monitored, if the current is lower than reverse current limit, the low-side synchronous rectifier is turned off, the high-side power switch is turned on. At the initial off-time, low-side synchronous rectifier current sample is disabled to make sampling noise shielding. The reverse current limit blank time is typical 60ns.

Output Under Voltage Protection (UVP)

If $V_{OUT} < \sim 50\%$ of the set point for approximately 20μs occurring when the output short circuit or the load current is much heavier than the maximum current capacity, the output under voltage protection (UVP) will be triggered, and the device will enter into hic-cup protection mode. The minimum hic-cup on time is 3ms, and the minimum hic-cup off time is 15ms. If the output fault conditions are removed, the device will go back to normal operation in the nearest hic-cup on time.



Output Over Voltage Protection (OVP)

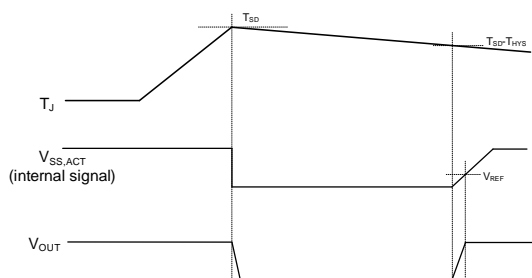
This device includes output over voltage protection (OVP). If the output voltage rises above the feedback regulation level, the high-side power switch naturally remains off and different actions are adopted in different operation mode.

When operating in PFM light load mode, if the output voltage remains higher than setting level, the low-side synchronous rectifier remains on until the inductor current reaches zero and the switching actions are suppressed. The switching actions will be recovered once the combined feedback and ramp signals become lower than the reference voltage. If the output voltage remains higher than OVP level for more than one OVP delay time, PG will turn from high to low.

When operating in FCCM light load mode, if the output voltage remains high, the reverse current limit will be triggered and inductor current average value becomes negative, trying to make output voltage lower. False OVP may happen under light load condition if the inductance is chosen too small and reverse current limit is triggered.

Over Temperature Protection (OTP)

Instant-PWM includes over temperature protection (OTP) circuitry to prevent overheating due to excessive power dissipation. This will shut down the device when the junction temperature exceeds 160°C. Once the junction temperature cools down by approximately 30°C, the device will resume normal operation after a complete soft-start cycle. For continuous operation, provide adequate cooling so that the junction temperature does not exceed the OTP threshold.



Thermal Design Considerations

Maximum power dissipation depends on the thermal resistance of the IC package, the PCB layout, the surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation may be calculated by:

$$P_{D,MAX} = (T_{J,MAX} - T_A) / \theta_{JA}$$

Where, $T_{J,MAX}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction to ambient thermal resistance.

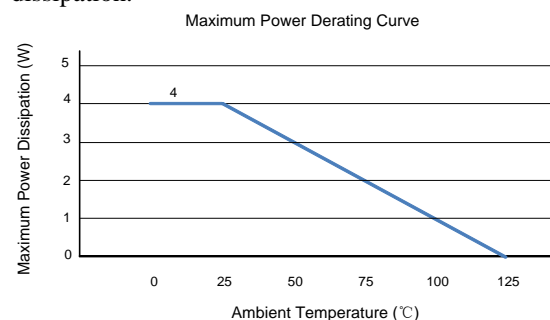
To comply with the recommended operating conditions, the maximum junction temperature is 125°C. The junction to ambient thermal resistance θ_{JA} is layout dependent. For the QFN3×4-21 package the thermal resistance θ_{JA} is 25°C/W when measured on a standard Silergy four-layer thermal test board. These standard thermal test layouts have a very large area with long 2oz. copper traces connected to each IC pin and very large, unbroken 1oz. internal power and ground planes.

Meeting the performance of the standard thermal test board in a typical tiny evaluation board area requires wide copper traces well-connected to the IC's backside pads leading to exposed copper areas on the component side of the board as well as good thermal via from the exposed pad connecting to a wide middle-layer ground plane and, perhaps, to an exposed copper area on the board's solder side.

The maximum power dissipation at $T_A=25^\circ\text{C}$ may be calculated by the following formula:

$$P_{D,MAX} = (125^\circ\text{C} - 25^\circ\text{C}) / (25^\circ\text{C/W}) = 4\text{W}$$

The maximum power dissipation depends on operating ambient temperature for fixed $T_{J,MAX}$ and thermal resistance θ_{JA} . Use the derating curve in figure below to calculate the effect of rising ambient temperature on the maximum power dissipation.

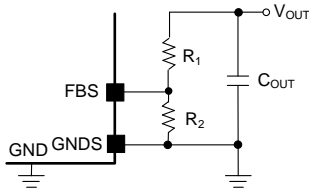


Design Procedure

Feedback Resistor Selection

Choose R_1 and R_2 to program the proper output voltage. To minimize the power consumption under light loads, it is desirable to choose large resistance values for both R_1 and R_2 . A value of between $10k\Omega$ and $1M\Omega$ is strongly recommended for both resistors. If V_{SET} is 1.2V, $R_1=100k\Omega$ is chosen, then using following equation, R_2 can be calculated to be $100k\Omega$.

$$R_2 = \frac{0.6V}{V_{SET} - 0.6V} \times R_1$$



Input Capacitor Selection

Input filter capacitors are needed to reduce the ripple voltage on the input, to filter the switched current drawn from the input supply and to reduce potential EMI. When selecting an input capacitor, be sure to select a voltage rating at least 20% greater than the maximum voltage of the input supply and a temperature rating above the system requirements. X5R or X7R series ceramic capacitors are most often selected due to their small size, low cost, surge current capability and high RMS current ratings over a wide temperature and voltage range. However, systems that are powered by a wall adapter or other long and therefore inductive cabling may be susceptible to significant inductive ringing at the input to the device. In these cases, consider adding some bulk capacitance like electrolytic, tantalum or polymer type capacitors. Using a combination of bulk capacitors (to reduce overshoot or ringing) in parallel with ceramic capacitors (to meet the RMS current requirements) is helpful in these cases.

Consider the RMS current rating of the input capacitor, paralleling additional capacitors if required to meet the calculated RMS ripple current,

$$I_{CIN_RMS} = I_{OUT} \times \sqrt{D \times (1-D)}$$

The worst-case condition occurs at $D = 0.5$, then

$$I_{CIN_RMS,MAX} = \frac{I_{OUT}}{2}$$

For simplification, choose an input capacitor with an RMS current rating greater than half of the maximum load current.

On the other hand, the input capacitor value determines the input voltage ripple of the converter. If there is an input voltage ripple requirement in the system, choose an appropriate input capacitor that meets the specification.

Given the very low ESR and ESL of ceramic capacitors, the input voltage ripple can be estimated by

$$V_{CIN_RIPPLE,CAP} = \frac{I_{OUT}}{f_{SW} \times C_{IN}} \times D \times (1-D)$$

The worst-case condition occurs at $D = 0.5$, then

$$V_{CIN_RIPPLE,CAP,MAX} = \frac{I_{OUT}}{4 \times f_{SW} \times C_{IN}}$$

The capacitance value is less important than the RMS current rating. In most applications two $22\mu F$ X5R capacitors is sufficient. Take care to locate the ceramic input capacitor as close to the device IN and GND pin as possible.

Inductor Selection

The inductor is necessary to supply constant current to the output load while being driven by the switched input voltage.

Instant-PWM operates well over a wide range of inductor values. This flexibility allows for optimization to find the best trade-off of efficiency, cost and size for a particular application. Selecting a low inductor value will help reduce size and cost and enhance transient response, but will increase peak inductor ripple current, reducing efficiency and increasing output voltage ripple. The low DC resistance (DCR) of these low value inductors may help reduce DC losses and increase efficiency. On the other hand, higher inductor values tend to have higher DCR and will slow transient response.

A reasonable compromise between size, efficiency, and transient response can be determined by selecting a ripple current (ΔI_L) about 20% ~ 50% of the desired full output load current. Start calculating the approximate inductor value by selecting the input and output voltages, the operating frequency (f_{SW}), the maximum output current ($I_{OUT,MAX}$) and estimating a ΔI_L as some percentage of that current.

$$L_1 = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times \Delta I_L}$$

Use this inductance value to determine the actual inductor ripple current (ΔI_L) and required peak current inductor current $I_{L,PEAK}$.

$$\Delta I_L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times L_1}$$

And $I_{L,PEAK} = I_{OUT,MAX} + \Delta I_L/2$

Select an inductor with a saturation current and thermal rating in excess of $I_{L,PEAK}$.

If FCCM light load operation is selected, make sure the inductor value is high enough to avoid reverse current limit is been triggered just under steady state if the load current is zero.

For highest efficiency, select an inductor with a low DCR that meets the inductance, size and cost targets. Low loss ferrite materials should be considered.

Inductor Design Example

Consider a typical design for a device providing $1.2V_{OUT}$ at 12A from $12V_{IN}$, operating at 600kHz and using target

inductor ripple current (ΔI_L) of 50% or 6A. Determine the approximate inductance value at first:

$$L_1 = \frac{1.2V \times (12V - 1.2V)}{12V \times 600kHz \times 6A} = 0.3\mu H$$

Next, select the nearest standard inductance value, in this case $0.33\mu H$, and calculate the resulting inductor ripple current (ΔI_L):

$$\Delta I_L = \frac{1.2V \times (12V - 1.2V)}{12V \times 600kHz \times 0.33\mu H} = 5.45A$$

$$I_{L,PEAK} = 12A + 5.45A/2 = 14.725A$$

The resulting 5.45A ripple current is $5.45A/12A$ is $\sim 45.4\%$, well within the 20% ~ 50% target.

$$I_{L,PEAK,RVS} = 5.45A/2 = 2.725A < I_{LIM,RVS}$$

Finally, select an available inductor with a saturation current higher than the resulting $I_{L,PEAK}$ of 14.725A.

Output Capacitor Selection

Instant-PWM provides excellent performance with a wide variety of output capacitor types. Ceramic and POS types are most often selected due to their small size and low cost. Total capacitance is determined by the transient response and output voltage ripple requirements of the system.

Output Ripple

Output voltage ripple at the switching frequency is caused by the inductor current ripple (ΔI_L) on the output capacitors ESR (ESR ripple) as well as the stored charge (capacitive ripple). When considering total ripple, both should be considered.

$$V_{RIPPLE,ESR} = \Delta I_L \times ESR$$

$$V_{RIPPLE,CAP} = \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}}$$

Consider a typical application with $\Delta I_L = 5.45A$ using two $22\mu F$ ceramic capacitors, each with an ESR of $\sim 5m\Omega$ for parallel total of $44\mu F$ and $2.5m\Omega$ ESR.

$$V_{RIPPLE,ESR} = 5.45A \times 2.5m\Omega = 13.6mV$$

$$V_{RIPPLE,CAP} = \frac{5.45A}{8 \times 44\mu F \times 600kHz} = 25.8mV$$

Total ripple = 39.4mV. The actual capacitive ripple may be higher than calculated value because the capacitance decreases with the voltage on the capacitor.

Using a $150\mu F$ 40m Ω POS cap, the above result is

$$V_{RIPPLE,ESR} = 5.45A \times 40m\Omega = 218mV$$

$$V_{RIPPLE,CAP} = \frac{5.45A}{8 \times 150\mu F \times 600kHz} = 7.56mV$$

Total ripple = 225mV

Output Transient Undershoot/Overshoot

If very fast load transient must be supported, consider the effect of the output capacitor on the output transient undershoot and overshoot. Instant-PWM responds quickly to changing load conditions, however, some considerations must

be needed, especially when using small ceramic capacitors which have low capacitance at low output voltages which results in insufficient stored energy for load transient. Output transient undershoot and overshoot have two causes: voltage changes caused by the ESR of the output capacitor and voltage changes caused by the output capacitance and inductor current slew rate.

ESR undershoot or overshoot may be calculated as $V_{ESR} = \Delta I_{OUT} \times ESR$. Using the ceramic capacitor example above and a fast load transient of $\pm 6A$, $V_{ESR} = \pm 6A \times 2.5m\Omega = \pm 15mV$. The POS capacitor result with the same load transient, $V_{ESR} = \pm 6A \times 40m\Omega = \pm 240mV$.

Capacitive undershoot (load increasing) is a function of the output capacitance, the load step, the inductor value and the input-output voltage difference and the maximum duty factor. During a fast load transient, the maximum duty factor of instant-PWM is a function of t_{ON} and the minimum t_{OFF} as the control scheme is designed to rapidly ramp the inductor current by grouping together many t_{ON} pulses in this case. The maximum duty factor D_{MAX} may be calculated by

$$D_{MAX} = \frac{t_{ON}}{t_{ON} + t_{OFF,MIN}}$$

Given this, the capacitive undershoot may be calculated by

$$V_{UNDERSHOOT,CAP} = -\frac{L_1 \times \Delta I_{OUT}^2}{2 \times C_{OUT} \times (V_{IN,MIN} \times D_{MAX} - V_{OUT})}$$

Consider a 6A load increase using the ceramic capacitor case when $V_{IN} = 12V$. At $V_{OUT} = 1.2V$, the result is $t_{ON} = 167ns$, $t_{OFF,MIN} = 150ns$, $D_{MAX} = 167 / (167 + 150) = 0.526$ and

$$V_{UNDERSHOOT,CAP} = -\frac{0.33\mu H \times (6A)^2}{2 \times 44\mu F \times (12V \times 0.526 - 1.2V)} = -26.4mV$$

Using the POS capacitor case, the above result is

$$V_{UNDERSHOOT,CAP} = -\frac{0.33\mu H \times (6A)^2}{2 \times 150\mu F \times (12V \times 0.526 - 1.2V)} = -7.7mV$$

Capacitive overshoot (load decreasing) is a function of the output capacitance, the inductor value and the output voltage.

$$V_{OVERSHOOT,CAP} = \frac{L_1 \times \Delta I_{OUT}^2}{2 \times C_{OUT} \times V_{OUT}}$$

Consider a 6A load decrease using the ceramic capacitor case above. At $V_{OUT} = 1.2V$ the result is

$$V_{OVERSHOOT,CAP} = \frac{0.33\mu H \times (6A)^2}{2 \times 44\mu F \times 1.2V} = 112.5mV$$

Using the POS capacitor case, the above result is

$$V_{OVERSHOOT,CAP} = \frac{0.33\mu H \times (6A)^2}{2 \times 150\mu F \times 1.2V} = 33mV$$

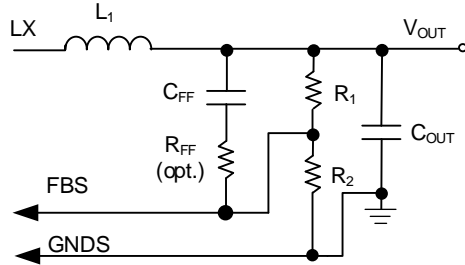
Combine the ESR and capacitive undershoot and overshoot to calculate the total overshoot and undershoot for a given application.

Load Transient Considerations:

The SQ29072 adopts the instant PWM architecture to achieve good stability and fast transient responses. In applications with

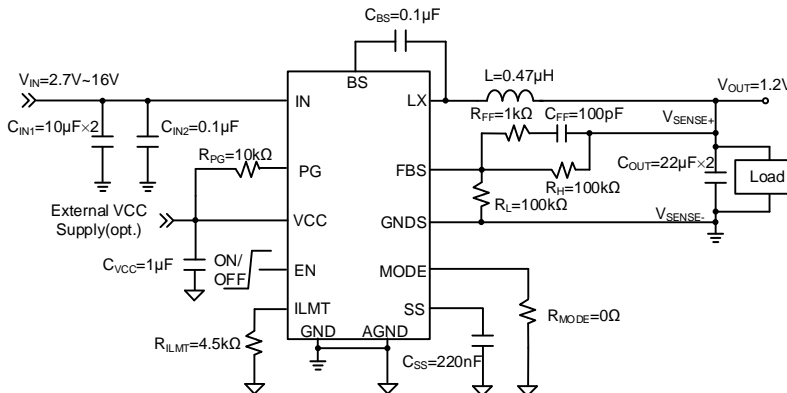
high step load current, adding an RC feed-forward compensation network R_{FF} and C_{FF} may further speed up the load transient responses. $R_{FF} = 1k\Omega$ and $C_{FF} = 220pF$ have been shown to perform well in most applications. Increase C_{FF} will speed up the load transient response if there is no stability issue.

Note that when $C_{OUT} > 500\mu F$ and minimum load current is low, set feed-forward values as $R_{FF} = 1k\Omega$ and $C_{FF} > 2.2nF$ to provide sufficient ripple to FB for small output ripple and good transient behavior.





Application Schematic (V_{OUT}=1.2V)



BOM List

Designator	Description	Part Number	Manufacturer
C _{IN1}	10μF/25V/X5R, 1206	GRM21BR61E106MA73L	mμRata
C _{IN2}	0.1μF/50V/X5R, 0603	GRM188R61H104KA93D	mμRata
C _{FF}	100pF/50V/C0G,0603	GRM1885C1H101JA01D	muRata
C _{OUT}	22μF/10V/X5R, 1206	GRM31CR61A226ME19L	mμRata
C _{SS}	220nF/50V/X5R, 0603	GRM188R61H224KAC4	mμRata
C _{BS}	0.1μF/50V/X5R, 0603	GRM188R61H104KA93D	mμRata
C _{VCC}	1.0μF/25V/X5R, 0603	GRM155R61E105KE11D	mμRata
L	0.47μH, inductor	PCMB104T-R47MS	CYNTEC
R _H	100kΩ, 1%, 0603		
R _L	100kΩ, 1%, 0603		
R _{PG}	10kΩ, 1%, 0603		
R _{MODE}	0Ω, 1%, 0603		
R _{ILMT}	4.5kΩ, 1%, 0603		
R _{FF}	1kΩ, 1%, 0603		

Recommend Table for Typical Applications

V _{OUT} (V)	R _H (kΩ)	R _L (kΩ)	C _{FF} (pF)	L/(Rated/Saturating Current)	C _{OUT}
1.2	100	100	100	0.47μH/(18A/20A)	22μF×2/10V/X7R,1206
1.8	100	49.9	100	0.47μH/(18A/20A)	22μF×2/10V/X7R,1206
3.3	100	22.1	220	0.68μH/(18A/20A)	22μF×2/10V/X7R,1206
5	100	13.7	220	1.0μH/(18A/20A)	22μF×2/10V/X7R,1206

Layout Design

Follow these PCB layout guidelines for optimal performance and thermal dissipation.

- Place the major MLCC capacitors (C_{IN} , C_{OUT} , C_{VCC}) on the same layer as the device.
- Place the input capacitor very near IN and GND, minimizing the loop formed by these connections. Avoid using direct vias connection in the power trace between the input capacitors and IN、GND to reduce parasitic inductance.
- Place one smaller package input MLCC capacitor at the reach out port of pin21. This capacitor can be connected with GND by vias.
- Place the VCC capacitor close to VCC using short, direct connections instead of vias connection to device GND pins.
- Make one Kelvin connection between AGND and GND at the C_{VCC} negative sides.
- Place the feedback components (R_1 , R_2 , R_{FF} and C_{FF}) as close to the FBS pin as possible. Avoid routing the remote output sense line and remote GND sense (GNDS) line near LX, BS or other high frequency signal as they are noise sensitive.
- Make the feedback sampling point Kelvin connect with C_{OUT} rather than the inductor output terminal.
- Guarantee the C_{OUT} negative sides are connected with GND pin by wide copper traces instead of vias, in order to achieve better accuracy and stability of output voltage.
- The LX connection has large voltage swings and fast edges and can easily radiate noise to adjacent components. Keep

its area small to prevent excessive EMI, while providing wide copper traces to minimize parasitic resistance and inductance. Keep sensitive components away from the switching node or provide ground traces between for shielding, to prevent stray capacitive noise pickup.

- Place the BS capacitor on the same layer as the device; keep the BS voltage path (BS, LX and C_{BS}) as short as possible.
- It is not recommended to connect control signals and IN directly. A resistor in a range of $1k\Omega$ to $1M\Omega$ should be used if they are pulled high by IN.
- Provide dedicated wide copper traces for the power path ground between the IC and the input and output capacitor grounds, rather than connecting each of these individually to an internal ground plane.
- The exposed GND pad should be connected to a large copper area and place several GND vias on it for heat sinking and to minimize noise.
- A four-layer layout is strongly recommended to achieve better thermal performance. $8.5cm \times 8.5cm$, four-layer PCB with 2-oz copper used as example.
- Keep the high current traces (IN, GND, LX and OUT trances) as short and wide as possible.
- The top layer and bottom layer should place power IN and GND copper plane as wide as possible. Middle1 layer should place all GND layer for conducting heat and shielding middle2 layer signal line from top layer crosstalk. Place signal lines on middle2 layer instead of other layers to avoid top and bottom GND layer be cut apart.

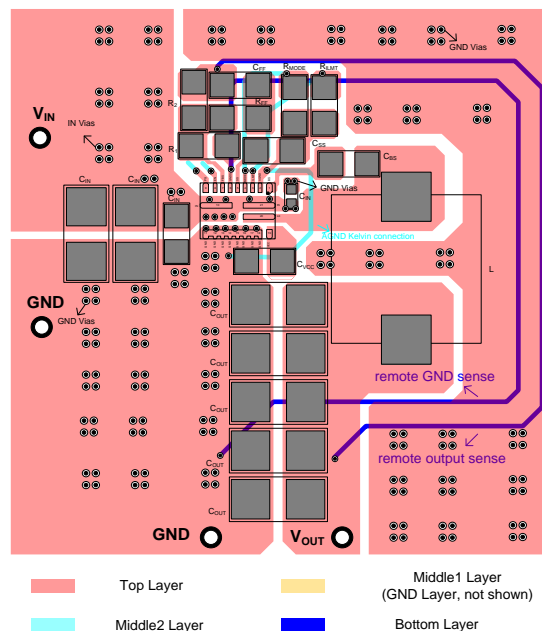
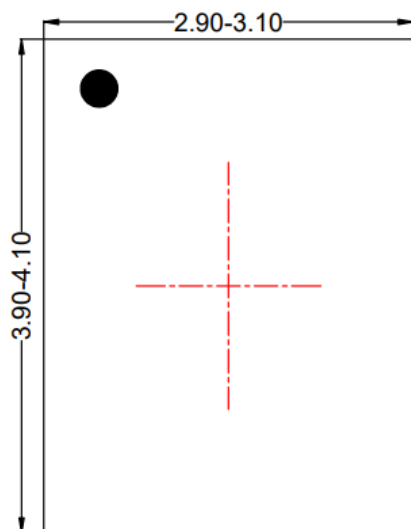
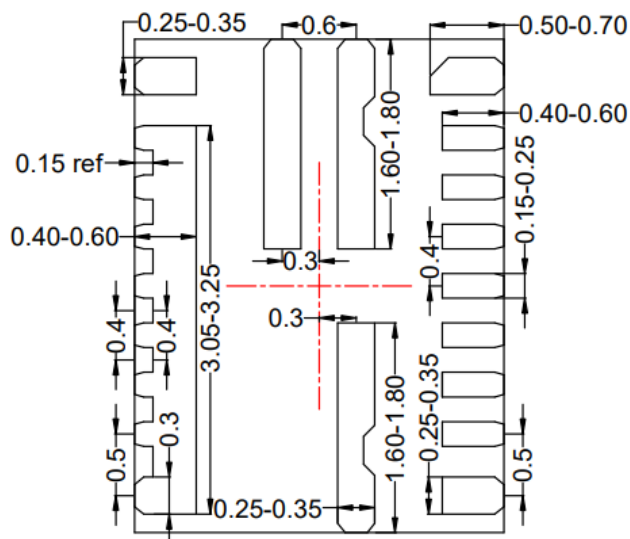


Figure4. PCB Layout Suggestion

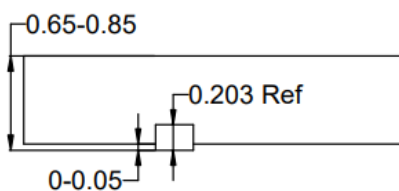
QFN3×4-21 Package Outline Drawing



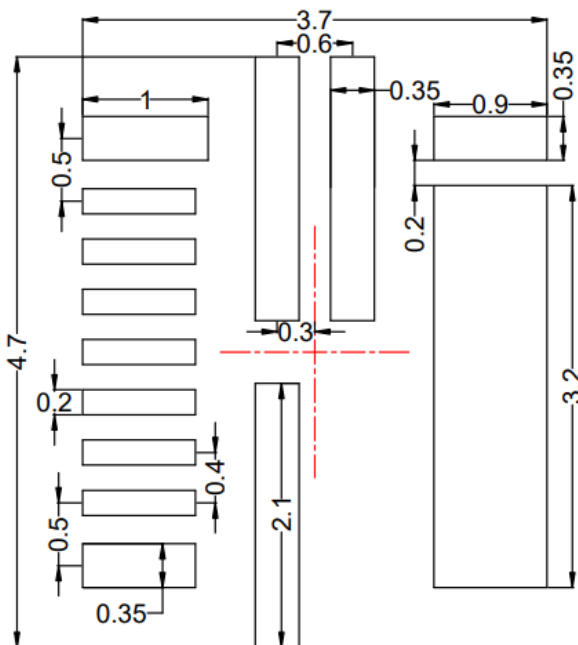
Top View



Bottom View



Front View

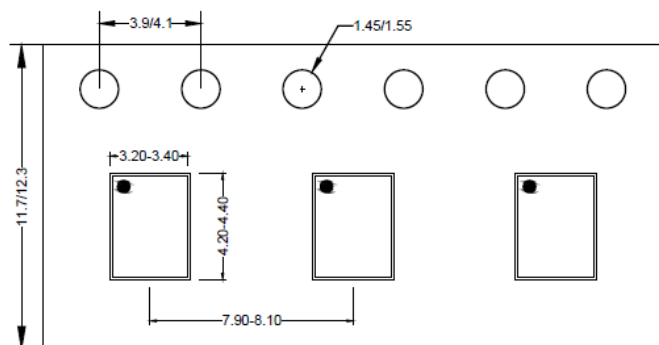


**Recommended PCB layout
(Reference only)**

Notes: 1, All dimension in millimeter and exclude mold flash & metal burr;
2, center line refers chip body center

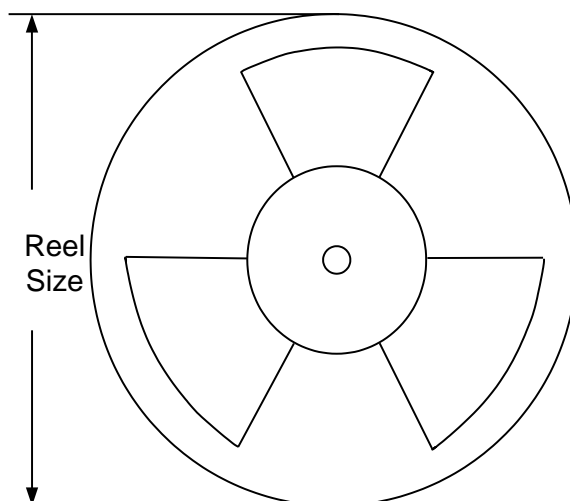
Taping & Reel Specification

1. Package orientation



Feeding direction →

2. Carrier Tape & Reel specification for packages



Package type	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Trailer length (mm)	Leader length (mm)	Qty per reel
QFN3×4	12	8	13"	400	400	5000

Revision History

Revision Number	Revision Date	Description	Pages changed
0.9	06/01/2021	Initial Release	-
0.9A	09/24/2021	The Absolute Maximum Ratings of the Supply Input Voltage changes from (-0.3V to 17V) to (-0.3V to 18V).	Page 3
0.9B	06/15/2022	Update the package outline drawing (Bottom View)	Page 18
1.0	03/07/2023	Upgrade the version code to Rev1.0 (No change in specification)	-
1.0A	05/31/2024	Update the package outline drawing	Page 20

Revision history is for reference only and may not be comprehensive or complete.

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